

#### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
	160mΩ @ V <sub>GS</sub> = 10V	2.9A
100V	200mΩ @ V <sub>GS</sub> = 4.5V	2.6A

### **Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

### **Applications**

- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

#### **Features and Benefits**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

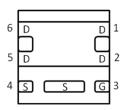
#### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0065 grams (Approximate)

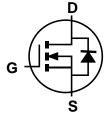
U-DFN2020-6 (Type E)



**Bottom View** 



Pin Out



**Equivalent Circuit** 

### Ordering Information (Note 4)

Part Number	Compliance	Case	Quantity Per Reel
DMN10H170SFDE-7	Standard	U-DFN2020-6 (Type E)	3,000
DMN10H170SFDE-13	Standard	U-DFN2020-6 (Type E)	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



# **Marking Information**

Site 1:



7H = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020)M = Month (ex: 9 = September)

Date Code Key

Year	2012		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Z		Н	I	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2:



7H = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: H = 2020)

W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

		2021	2022	2023	2024	2025	2026	2027	2028	2029
Code 2	0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	z

ĺ	Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
ſ	Code	Т	U	V	W	X	Υ	Z



### **Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	100	V		
Gate-Source Voltage			Vgss	±20	V
Continuous Dunis Courset (Nata C) V 40V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	2.9 2.3	А
Continuous Drain Current (Note 6) Vos = 10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	lo	3.4 2.7	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	)		I <sub>DM</sub>	10	Α
Maximum Body Diode Continuous Current		Is	2.5	Α	
Avalanche Current (Note 7)	las	4.7	Α		
Avalanche Energy (Note 7)			Eas	16	mJ

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	D-	0.66	W
Total Power Dissipation (Note 5)	$T_A = +70$ °C	PD	0.42	VV
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	189	°C/W
	t<10s	$R_{\theta JA}$	132	C/VV
Total Dawer Dissination (Note 6)	$T_A = +25$ °C	D-	2.03	W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	PD	1.31	VV
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	61	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	RθJA	43	
Thermal Resistance, Junction to Case (Note 6)		R <sub>θ</sub> JC	9.3	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# **Electrical Characteristics** (@ $T_A = \pm 25$ °C, unless otherwise specified.)

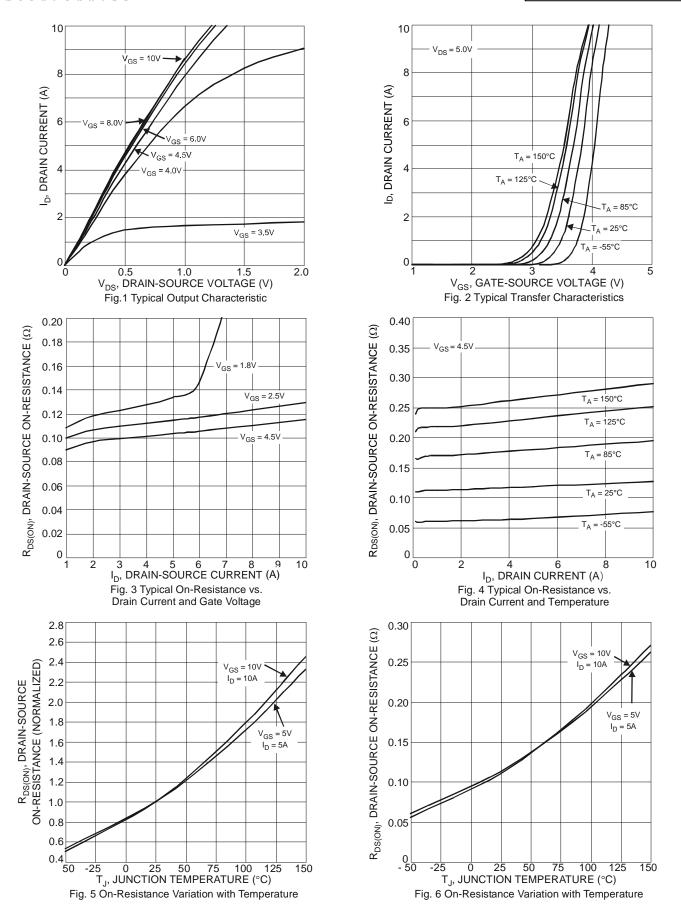
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BVDSS	100	1	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	_	1	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	2.0	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	D		116	160	mΩ	$V_{GS} = 10V, I_{D} = 5.0A$
Static Drain-Source On-Resistance	RDS(ON)	_	126	200	11122	V <sub>GS</sub> = 4.5V, I <sub>D</sub> =5.0A
Diode Forward Voltage	VsD	_	0.9	1.0	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 10A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C <sub>iss</sub>	_	1167		рF	.,
Output Capacitance	Coss	_	36	_	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, -f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	25	_	pF	1 = 1.0WH IZ
Gate Resistance	Rg	_	1.3	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	4.9	_	nC	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	9.7	_	nC	\/ 00\/ I- 40.04
Gate-Source Charge	Qgs	_	2.0	_	nC	$V_{DS} = 80V, I_{D} = 12.8A$
Gate-Drain Charge	Q <sub>gd</sub>	_	2.0	_	nC	]
Turn-On Delay Time	tD(ON)	_	10.5	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	11.1	_	ns	V <sub>DS</sub> = 50V, I <sub>D</sub> = 12.8A
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	42.6	_	ns	$V_{GS} = 10V$ , $R_{G} = 25\Omega$
Turn-Off Fall Time	tF	_	12.8	_	ns	
Reverse Recovery Time	trr	_	30.3	_	ns	1 40.00 41/44 4000/
Reverse Recovery Charge	Q <sub>RR</sub>	_	35.2	_	nC	I <sub>F</sub> = 12.8A, di/dt = 100A/μs

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7. UIS in production with L = 1.43mH,  $T_J = +25$ °C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.











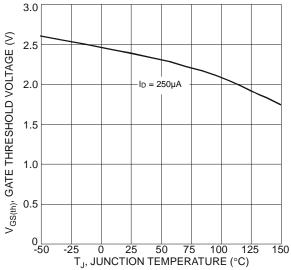
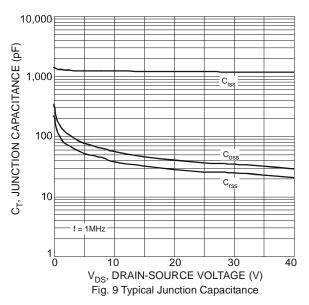
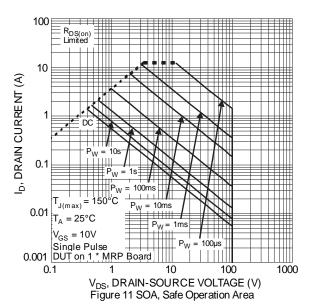
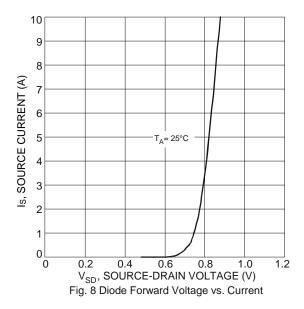
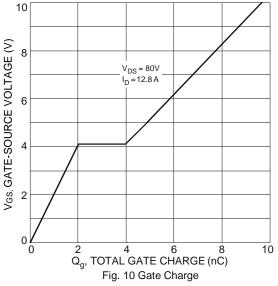


Fig. 7 Gate Threshold Variation vs. Junction Temperature

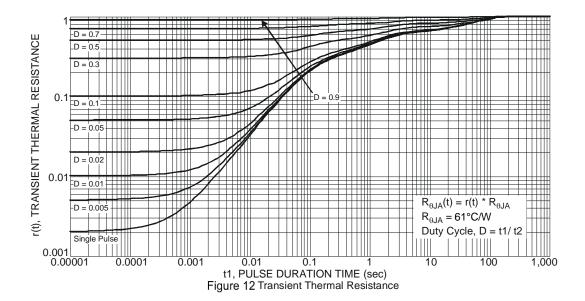










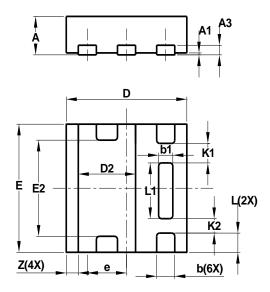




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type E)

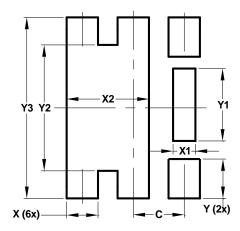


U-DFN2020-6 Type E								
Dim								
Α	0.57	0.63	0.60					
A1	0	0.05	0.03					
A3	_		0.15					
b	0.25	0.35	0.30					
b1	0.185	0.285	0.235					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
Е	1.95	2.05	2.00					
E2	1.40	1.60	1.50					
е	_	_	0.65					
L	0.25	0.35	0.30					
L1	0.82	0.92	0.87					
K1	_	_	0.305					
K2	_	_	0.225					
Z	_	_	0.20					
All	Dimens	ions in r	nm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300



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